

**HIGH EFFICIENCY HETEROJUNCTION POWER FET CHIP (.25μm x 200μm)**

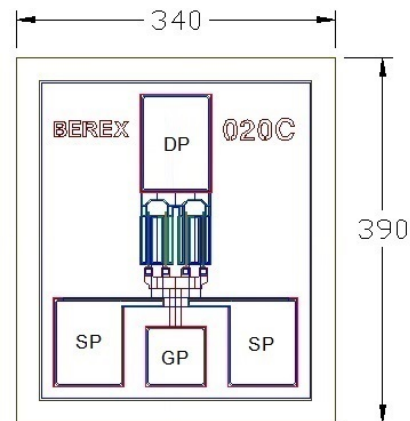
The BeRex BCP020C is a GaAs Power pHEMT with a nominal 0.25-micron by 200-micron gate making this product ideally suited for applications where high-gain and medium power in the DC to 26.5 GHz frequency range are required. The product may be used in either wideband (6-18 GHz) or narrow-band applications. The BCP020C is produced using state of the art metallization with Si<sub>3</sub>N<sub>4</sub> passivation and is screened to assure reliability.

**PRODUCT FEATURES**

- 22 dBm Typical Output Power
- 14 dB Typical Gain @ 12 GHz
- 0.25 X 200 Micron Recessed Gate

**APPLICATIONS**

- Commercial
- Military / Hi-Rel.
- Test & Measurement



Chip dimensions : 340 X 390 microns  
 Gate pad(GP) : 60 X 60 microns  
 Drain pad(DP) : 70 X 100 microns  
 Source pad(SP) : 70 X 95 microns  
 Chip thickness : 75 microns

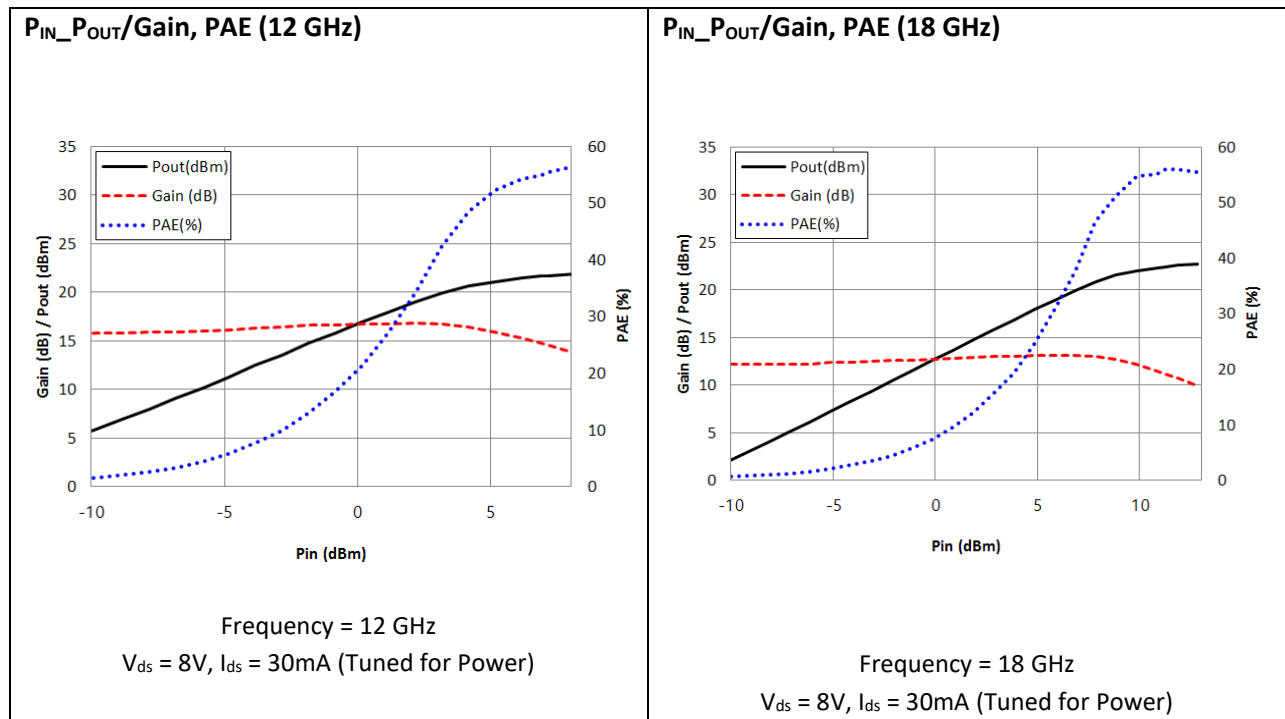
**ELECTRICAL CHARACTERISTIC (TUNED FOR POWER) T<sub>a</sub> = 25° C**

PARAMETER/TEST CONDITIONS		TEST FREQ.	MIN.	TYPICAL	MAX.	UNIT
P <sub>1dB</sub>	Output Power @ P <sub>1dB</sub> (V <sub>ds</sub> = 8V, I <sub>d</sub> = 30mA)	12 GHZ 18 GHZ	20.5 20.5	22.0 22.0		dBm
G <sub>1dB</sub>	Gain @ P <sub>1dB</sub> (V <sub>ds</sub> = 8V, I <sub>d</sub> = 30mA)	12 GHZ 18 GHZ	12.5 9.5	14.0 11.0		dB
PAE	PAE @ P <sub>1dB</sub> (V <sub>ds</sub> = 8V, I <sub>d</sub> = 30mA)	12 GHZ 18 GHZ		55 55		%
NF	Noise figure (V <sub>ds</sub> = 2V, I <sub>d</sub> = 10 mA)	12 GHZ		1.05		dB
I <sub>dss</sub>	Saturated Drain Current (V <sub>gs</sub> = 0V, V <sub>ds</sub> = 2.0V)		40	60	80	mA
G <sub>m</sub>	Transconductance (V <sub>ds</sub> = 2V, I <sub>d</sub> = 30mA)			78		mS
V <sub>p</sub>	Pinch-off Voltage (I <sub>ds</sub> = 0.2mA, V <sub>ds</sub> = 2V)		-2.5	-1.2		V
BV <sub>gd</sub>	Drain Breakdown Voltage (I <sub>g</sub> = -0.2mA, source open)			-15	-12	V
BV <sub>gs</sub>	Source Breakdown Voltage (I <sub>g</sub> = -0.2mA, drain open)			-13		V
R <sub>th</sub>	Thermal Resistance (Au-Sn Eutectic Attach)			155		°C/W

**MAXIMUM RATING (T<sub>a</sub> = 25° C)**

PARAMETERS		ABSOLUTE	CONTINUOUS
V <sub>ds</sub>	Drain-Source Voltage	12V	8 V
V <sub>gs</sub>	Gate-Source Voltage	-6V	-3 V
I <sub>d</sub>	Drain Current	I <sub>dss</sub>	I <sub>dss</sub>
I <sub>gf</sub>	Forward Gate Current	11 mA	2 mA
P <sub>in</sub>	Input Power	17 dBm	@ 3dB compression
T <sub>ch</sub>	Channel Temperature	175°C	150°C
T <sub>stg</sub>	Storage Temperature	-60°C – 150°C	-60°C – 150°C
P <sub>t</sub>	Total Power Dissipation	1.0 W	0.8 W

Exceeding any of the above Maximum Ratings will result in reduced MTTF and may cause permanent damage to the device.

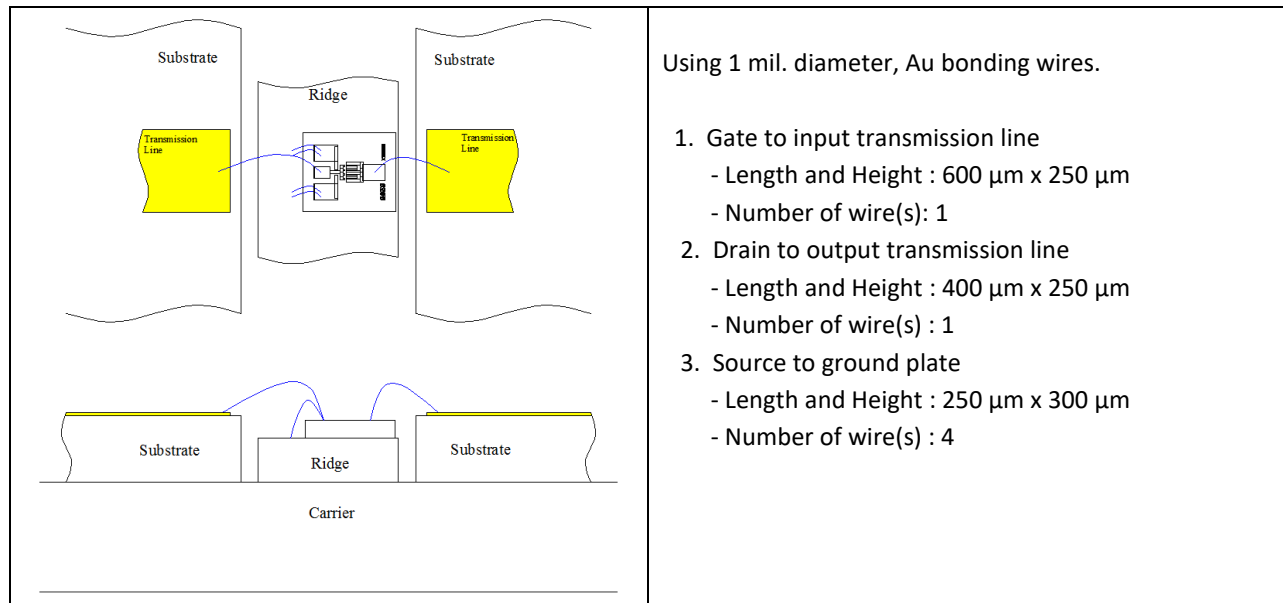


S-PARAMETERS ( $V_{ds} = 8V$ ,  $I_{ds} = 30mA$ )

FREQ. [GHZ]	S11 [MAG]	S11 [ANG.]	S21 [MAG]	S21 [ANG.]	S12 [MAG]	S12 [ANG.]	S22 [MAG]	S22 [ANG.]
1.0	0.99	-15.31	4.97	167.46	0.012	81.67	0.88	-4.21
2.0	0.97	-29.80	4.85	156.22	0.020	72.74	0.87	-8.78
3.0	0.94	-44.22	4.73	145.14	0.030	68.00	0.85	-13.28
4.0	0.90	-60.25	4.60	134.20	0.037	62.14	0.84	-16.02
5.0	0.86	-76.06	4.47	123.09	0.044	52.91	0.82	-19.39
6.0	0.82	-92.31	4.32	111.94	0.048	44.59	0.79	-23.31
7.0	0.78	-109.93	4.13	101.26	0.055	39.19	0.77	-25.87
8.0	0.74	-126.99	3.93	90.75	0.056	32.28	0.75	-28.39
9.0	0.71	-144.87	3.70	80.05	0.058	25.93	0.72	-31.61
10.0	0.70	-162.63	3.44	70.00	0.059	19.00	0.71	-34.00
11.0	0.70	-179.42	3.17	60.31	0.057	16.14	0.68	-36.81
12.0	0.72	165.74	2.92	50.94	0.056	9.46	0.66	-39.98
13.0	0.74	152.86	2.69	42.87	0.056	6.43	0.64	-41.91
14.0	0.76	142.52	2.47	35.44	0.055	3.83	0.62	-44.64
15.0	0.79	132.78	2.28	27.88	0.053	2.00	0.60	-47.32
16.0	0.80	125.13	2.10	21.28	0.053	2.02	0.58	-50.59
17.0	0.83	118.62	1.97	14.85	0.054	-1.25	0.57	-55.47
18.0	0.84	111.90	1.83	8.08	0.054	-2.67	0.56	-60.16
19.0	0.85	107.02	1.69	1.45	0.056	-5.19	0.55	-67.17
20.0	0.86	101.87	1.56	-5.08	0.059	-8.40	0.54	-75.07
21.0	0.86	98.40	1.46	-11.21	0.060	-10.88	0.53	-82.70
22.0	0.85	95.28	1.35	-17.15	0.062	-11.32	0.53	-90.96
23.0	0.84	92.18	1.25	-23.39	0.058	-12.62	0.53	-99.81
24.0	0.85	90.39	1.16	-28.76	0.060	-13.27	0.53	-109.02
25.0	0.86	88.89	1.08	-33.55	0.058	-10.59	0.53	-117.73
26.0	0.87	85.43	0.99	-39.26	0.058	-4.61	0.54	-125.41

Note: S-parameters include bond wires. Reference planes are at edge of substrates shown on "Wire Bonding Information" figure below.

## WIRE BONDING INFORMATION



Proper ESD procedures should be followed when handling this device.

**DIE ATTACH RECOMMENDATIONS:**

BeRex recommends the “Eutectic” die attach using Au-Sn (80%-20%) pre-forms. The die attach station must have accurate temperature control, and the operation should be performed with parts no hotter than 300°C for less than 60 seconds. An inert forming gas (90% N<sub>2</sub>-10% H<sub>2</sub>) or clean, dry N<sub>2</sub> should be used.

Use of conductive epoxy (gold or silver filled) may also be acceptable for die-attaching low power devices.

**HANDLING PRECAUTIONS:**

GaAs FETs are very sensitive to and may be damaged by Electrostatic Discharge (ESD). Therefore, proper ESD precautions must be taken whenever you are handling these devices. It is critically important that all work surfaces, and assembly equipment, as well as the operator be properly grounded when handling these devices to prevent ESD damage.

**STORAGE & SHIPPING:**

The BeRex standard chip device shipping package consists of an antistatic “Gel-Pak”, holding the chips, placed inside a sealed antistatic and moisture barrier bag. This packaging is designed to provide a reasonable measure of protection from both mechanical and ESD damage.

Chip devices should be stored in a clean, dry Nitrogen gas environment at room temperature until they are required for assembly. Only open the shipping package or perform die assembly in a work area with a class 10,000 or better clean room environment to prevent contamination of the exposed devices.

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.